

isc Silicon NPN Power Transistor

DESCRIPTION

- · High Breakdown Voltage-
 - : V_{(BR)CBO}= 1500V(Min)
- · High Switching Speed
- High Reliability
- Built-in Damper Diode
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

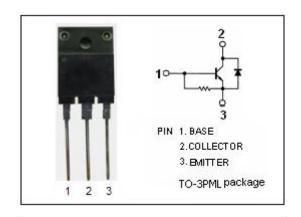


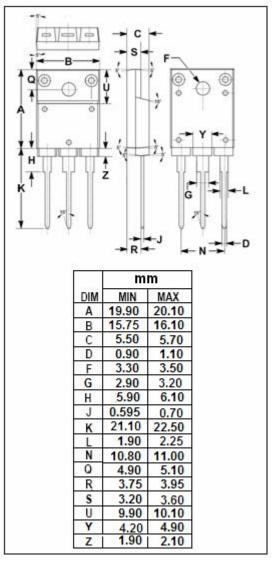
APPLICATIONS

 Ultrahigh-definition CRT display horizontal deflection output applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|--|-------|------------|--|
| V _{CBO} | Collector-Base Voltage | 1500 | V | |
| Vceo | Collector-Emitter Voltage | 800 | V | |
| V _{EBO} | Emitter-Base Voltage | 6 | V | |
| Ic | Collector Current-Continuous | 8 | А | |
| I _{CP} | Collector Current-Peak | 25 | А | |
| Pc | Collector Power Dissipation @ T _a =25℃ | 3.0 | W | |
| | Collector Power Dissipation @ T _C =25°C | 70 | | |
| TJ | Junction Temperature | 150 | $^{\circ}$ | |
| T _{stg} | Storage Temperature Range -55 | | $^{\circ}$ | |







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2SC4124

ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

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|------------------------------------|--------------------------------------|--|-----|------|-----|------|--|--|--|
| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | | | |
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 10mA; I _B = 0 | 800 | | | V | | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | Ic= 6A; I _B = 1.5A | | | 5.0 | V | | | |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 6A; I _B = 1.5A | | | 1.5 | V | | | |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 800V; I _E = 0 | | | 10 | μА | | | |
| Ices | Collector Cutoff Current | V _{CE} = 1500V; R _{BE} = 0 | | | 1.0 | mA | | | |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 4V; I _C = 0 | 40 | | 130 | mA | | | |
| h _{FE-1} | DC current gain | I _C = 1A; V _{CE} = 5V | 8 | | | | | | |
| h _{FE-2} | DC current gain | Ic= 6A; V _{CE} = 5V | 4 | | 6 | | | | |
| Switching times | | | | | | | | | |
| t _{stg} | Storage Time | I _C = 6A, I _{B1} = 1.2A; I _{B2} = -2.4A | | | 3.0 | μS | | | |
| t _f | Fall Time | R _L = 33.3Ω ; V _{CC} = $200V$ | | | 0.2 | μs | | | |

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